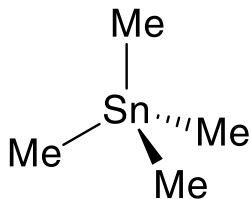


Catalog # 50-1900 Tetramethyltin, 98%



Thermal Behavior:

- Melting point: -54°C
- Boiling point: 76-78°C
- Vapor pressure: 110 Torr/25°C

Technical Notes:

1. ALD/CVD and dopant for tin containing thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
SnO ₂	CVD	23°C	7 Torr	O ₃	350°C	1
	ALD	-	AP	NO ₂	250°C	2
CdO:Sn	CVD	17°C	AP	CdMe ₂ , Te/Pr ₃	200-300°C	3
ZnSnO _x	PE-CVD	RT	10 mTorr	ZnEt ₂ , O ₂	RT	4
Sn:Bi ₂ Te ₃	CVD	0°C	AP	Me ₃ Bi, /Pr ₂ Te, H ₂	360°C	5

References:

1. [J. Electrochem. Soc. 2007, 154, D34.](#)
2. [Electrochem. Solid-State Lett. 2010, 13, G75.](#)
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4. [Adv. Mater. Res. 2007, 26-28, 515.](#)
5. [Appl. Surf. Sci. 2015, 353, 232.](#)